1PS66SB63; 1PS79SB63

5 V, 20 mA low C_d Schottky barrier diodes Rev. 02 — 3 December 2004

Product data sheet

Product profile 1.

1.1 General description

Planar low capacitance Schottky barrier diodes encapsulated in ultra small SMD plastic packages.

Table 1: **Product overview**

Type number	Package		Package Config		Configuration
	Philips	JEITA			
1PS66SB63	SOT666	-	triple isolated diode		
1PS79SB63	SOD523	SC-79	single diode		

1.2 Features

- Very low diode capacitance
- Very low forward voltage
- Ultra small SMD plastic packages.

1.3 Applications

- Digital applications:
 - Ultra high-speed switching
 - Clamping circuits.
- RF applications:
 - ◆ Diode ring mixer
 - RF detector
 - RF voltage doubler.

1.4 Quick reference data

Table 2: Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	continuous forward current		-	-	20	mA
V_R	continuous reverse voltage		-	-	5	V
C _d	diode capacitance	$V_R = 0 V;$ f = 1 MHz; see <u>Figure 3</u>	-	0.35	0.5	pF



2. Pinning information

Table 3: Pinning

Pin	Description	Simplified outline	Symbol
1PS66SE	B63 (SOT666)		
1	anode (diode 1)	·	
2	anode (diode 2)	6 5 4	6 5 4
3	anode (diode 3)		(法 法 法)
4	cathode (diode 3)		1 2 3
5	cathode (diode 2)	0	sym046
6	cathode (diode 1)	1	
1PS79SE	B63 (SOD523)		
1	cathode	[1]	
2	anode	1 2	1 - 2
			sym001
		Top view	

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 4: Ordering information

Type number	Package	Package				
	Name	Description	Version			
1PS66SB63	-	plastic surface mounted package; 6 leads	SOT666			
1PS79SB63	SC-79	plastic surface mounted package; 2 leads	SOD523			

4. Marking

Table 5: Marking codes

Type number	Marking code
1PS66SB63	N4
1PS79SB63	T1

5. Limiting values

Table 6: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{R}	continuous reverse voltage		-	5	V
l _F	continuous forward current		-	20	mA
Tj	junction temperature		-	125	°C
T _{amb}	ambient temperature		-65	+125	°C
T _{stg}	storage temperature		-65	+150	°C

6. Thermal characteristics

Table 7: Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	SOT666		[2] [3]	-	700	K/W
	SOD523		<u>[4]</u> _	-	450	K/W

^[1] For Schottky barrier diodes thermal run-away has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determining the reverse power losses P_R and $I_{F(AV)}$ rating will be available on request.

7. Characteristics

Table 8: Characteristics

 $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

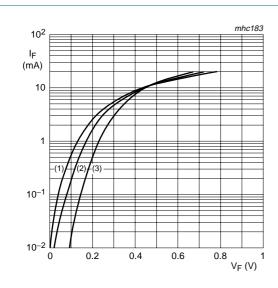
			Тур	Max	Unit
forward voltage	see Figure 1;	<u>[1]</u>			
	I _F = 0.1 mA	-	160	200	mV
	I _F = 1 mA	-	240	300	mV
reverse current	see Figure 2;				
	V _R = 1 V	-	0.4	1	μΑ
	V _R = 5 V	-	-	50	μΑ
diode capacitance	$V_R = 0 V$; $f = 1 MHz$; see Figure 3	-	0.35	0.5	pF
series inductance		-	0.6	-	nΗ
	reverse current diode capacitance	$I_{F} = 0.1 \text{ mA}$ $I_{F} = 1 \text{ mA}$ $I_{F} = 1 \text{ mA}$ $V_{R} = 1 \text{ V}$ $V_{R} = 5 \text{ V}$ $V_{R} = 0 \text{ V}; f = 1 \text{ MHz};$ $V_{R} = 0 \text{ V}; f = 1 \text{ MHz};$ $V_{R} = 0 \text{ V}; f = 1 \text{ MHz};$ $V_{R} = 0 \text{ V}; f = 1 \text{ MHz};$ $V_{R} = 0 \text{ V}; f = 1 \text{ MHz};$	$I_{F} = 0.1 \text{ mA} \qquad - \\ I_{F} = 1 \text{ mA} \qquad - \\ \text{reverse current} \qquad \frac{\text{see Figure 2};}{\text{V}_{R} = 1 \text{ V}} \qquad - \\ \text{V}_{R} = 5 \text{ V} \qquad - \\ \text{diode} \qquad \text{V}_{R} = 0 \text{ V}; \text{f = 1 MHz}; \qquad - \\ \text{capacitance} \qquad \text{see Figure 3}$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	

^[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

^[2] Refer to SOT666 standard mounting conditions.

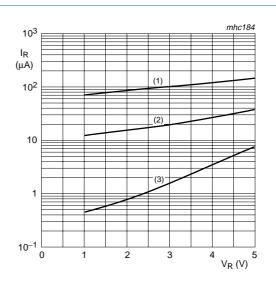
^[3] Reflow soldering is the only recommended soldering method.

^[4] Refer to SOD523 (SC-79) standard mounting conditions.



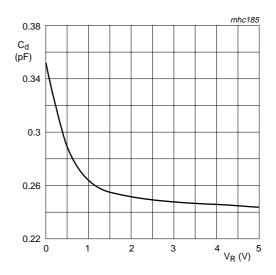
- (1) $T_{amb} = 125 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \,^{\circ}C$.

Fig 1. Forward current as a function of forward voltage; typical values



- (1) $T_{amb} = 125 \,^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig 2. Reverse current as a function of reverse voltage; typical values



 $T_{amb} = 25 \, ^{\circ}C$; f = 1 MHz.

Fig 3. Diode capacitance as a function of reverse voltage; typical values

8. Package outline

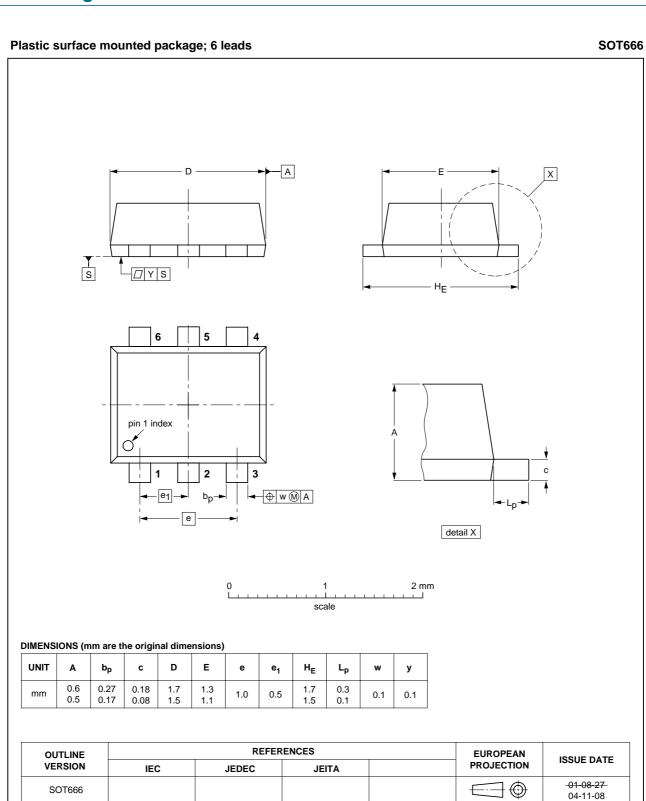


Fig 4. Package outline SOT666

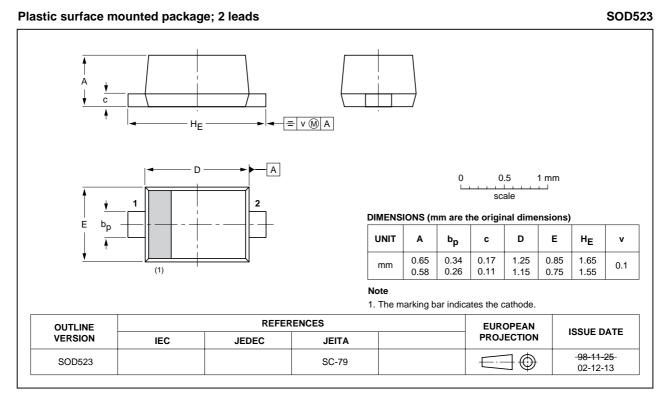


Fig 5. Package outline SOD523 (SC-79)



9. Packing information

Table 9: Packing methods

The -xxx numbers are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description	Packing q	Packing quantity	
			3000	4000	10000
1PS66SB63	SOT666	4 mm pitch, 8 mm tape and reel	-	-115	-
1PS79SB63	SOD523	4 mm pitch, 8 mm tape and reel	-115	-	-135

^[1] For further information and the availability of packing methods see Section 14.



10. Revision history

Table 10: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
1PS66SB63_1PS79SB63_2	20041203	Product data sheet	-	9397 750 13846	1PS79SB63_1
Modifications: • The format of this data sheet has been redesigned to comply with the new presentatio and information standard of Philips Semiconductors				new presentation	
	 Type numb 	oer 1PS66SB63 added	l.		
1PS79SB63_1	20020408	Product specification	-	9397 750 09483	-



Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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- [1] Please consult the most recently issued data sheet before initiating or completing a design.
- [2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
- [3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

12. Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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For sales office addresses, send an email to: sales.addresses@www.semiconductors.philips.com

1PS66SB63; 1PS79SB63

Philips Semiconductors

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